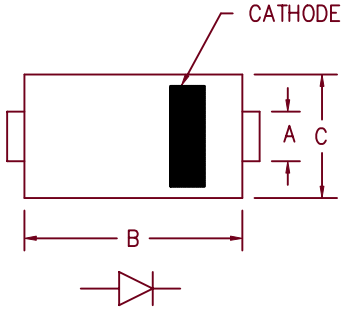
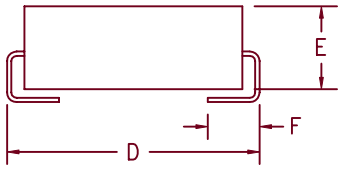
1 Amp Ultra Low Forward Voltage Schottky Diode

LSM115J



Dim.	Inches		Millimeter		
	Minimum	Maximum	Minimum	Maximum	Notes
A	.073	.087	1.85	2.21	
B	.160	.180	4.06	4.57	
C	.130	.155	3.30	3.94	
D	.205	.220	5.21	5.59	
E	.075	.130	1.91	3.30	
F	.030	.060	.760	1.52	



DO-214BA Package

Microsemi Catalog Number	Working Peak Reverse Voltage	Repetitive Peak Reverse Voltage
LSM115J	15V	15V

- Schottky Barrier Rectifier
- Guard Ring For Reverse Protection
- Low Power Loss, High Efficiency
- 100°C Junction Temperature
- V_{RRM} 15V
- High Surge Capability
- Ultra Low Forward Voltage
- Schottky OR'ing diode

Electrical Characteristics

Average forward current	$I_{F(AV)}$ 1 Amps	T_L = 65°C, Square wave, $R_{\theta JL}$ = 15°C/W
Maximum surge current	I_{FSM} 50 Amps	8.3ms, half sine, T_J = 100°C
Maximum peak forward voltage	V_{FM} 0.29 Volts	I_{FM} = 1.0A; T_J = 25°C*
Maximum peak reverse current	I_{RM} 500 mA	V_{RRM} = 15V, T_J = 100°C
Maximum peak reverse current	I_{RM} 200 mA	V_R = 5V, T_J = 100°C
Maximum peak reverse current	I_{RM} 100 mA	V_R = 3.3V, T_J = 100°C
Maximum peak reverse current	I_{RM} 10 mA	V_{RRM} = 15V, T_J = 25°C
Typical junction capacitance	C_J 120pF	T_J = 25°C, V_R = 5V

*Pulse test: Pulse width 300 μsec. Duty cycle 2%

Thermal and Mechanical Characteristics

Storage temperature range	T_{STG}	−55°C to 150°C
Operating junction temp range	T_J	−55°C to 100°C
Maximum thermal resistance	$R_{\theta JL}$	15°C/W Junction to Lead
Weight		.0047 ounces (.013 grams) typical

4-3-00 Rev. 2

COLORADO Microsemi
800 Hoyt Street
Broomfield, CO. 80020
PH: (303) 469-2161
FAX: (303) 466-3775
www.microsemi.com

LSM115J

Figure 1
Typical Forward Characteristics

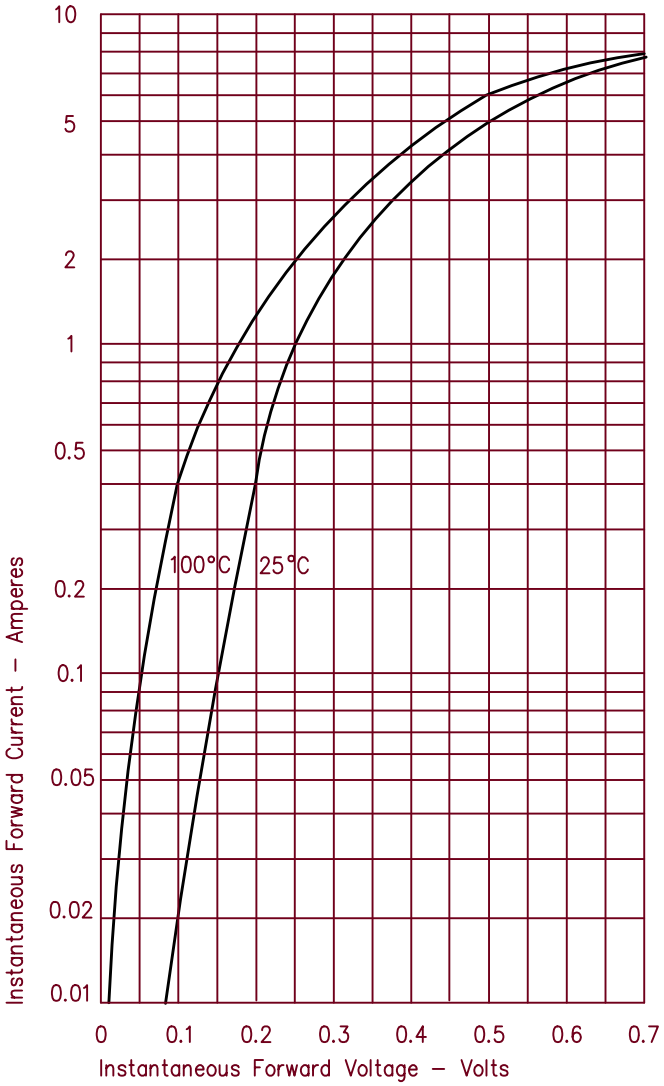


Figure 3
Typical Junction Capacitance

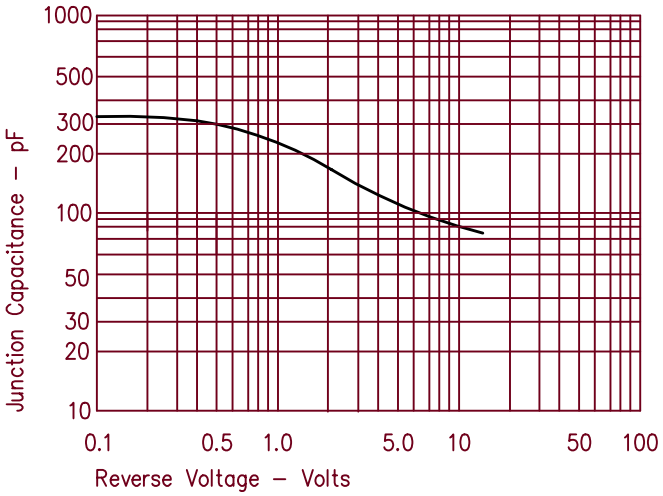


Figure 2
Typical Reverse Characteristics

